

Silicon PNP Power Transistors

2SA1471

DESCRIPTION

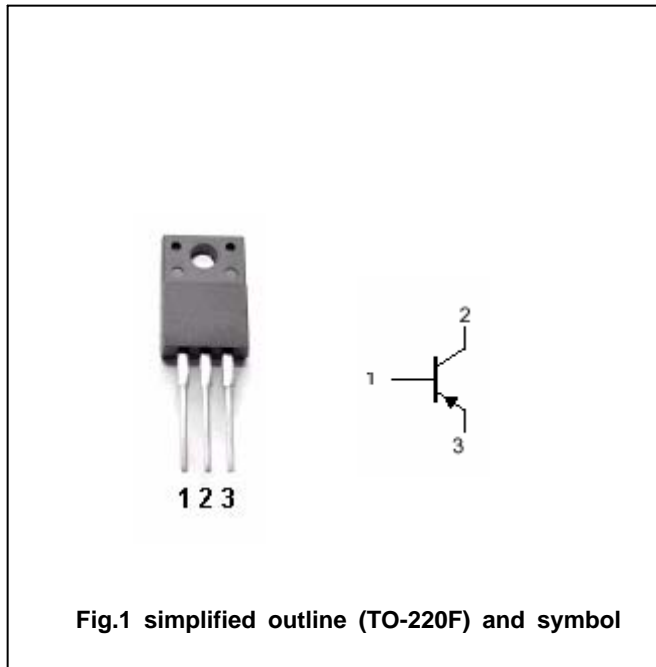
- With TO-220Fpackage
- Low saturation voltage.
- Complement to type 2SC3748
- Fast switching speed.

APPLICATIONS

- Car-use inductance drivers, lamp drivers.
- Inverters drivers, converters
- Power amplifications
- Switching regulators,drivers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-10	A
I _{CM}	Collector current-peak		-12	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	30	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA; I _E =0	-80			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; R _{BE} =	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.25A			-0.4	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-1A; V _{CE} =-2V	70		280	
f _T	Transition frequency	I _C =-1A; V _{CE} =-5V		100		MHz

Switching times

t _{on}	Turn-on time	V _{CC} =20V; I _C =5A I _{B1} =-I _{B2} =-0.25A R _L =4		0.1		μs
t _{stg}	Storage time			0.5		μs
t _f	Fall time			0.1		μs

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PACKAGE OUTLINE

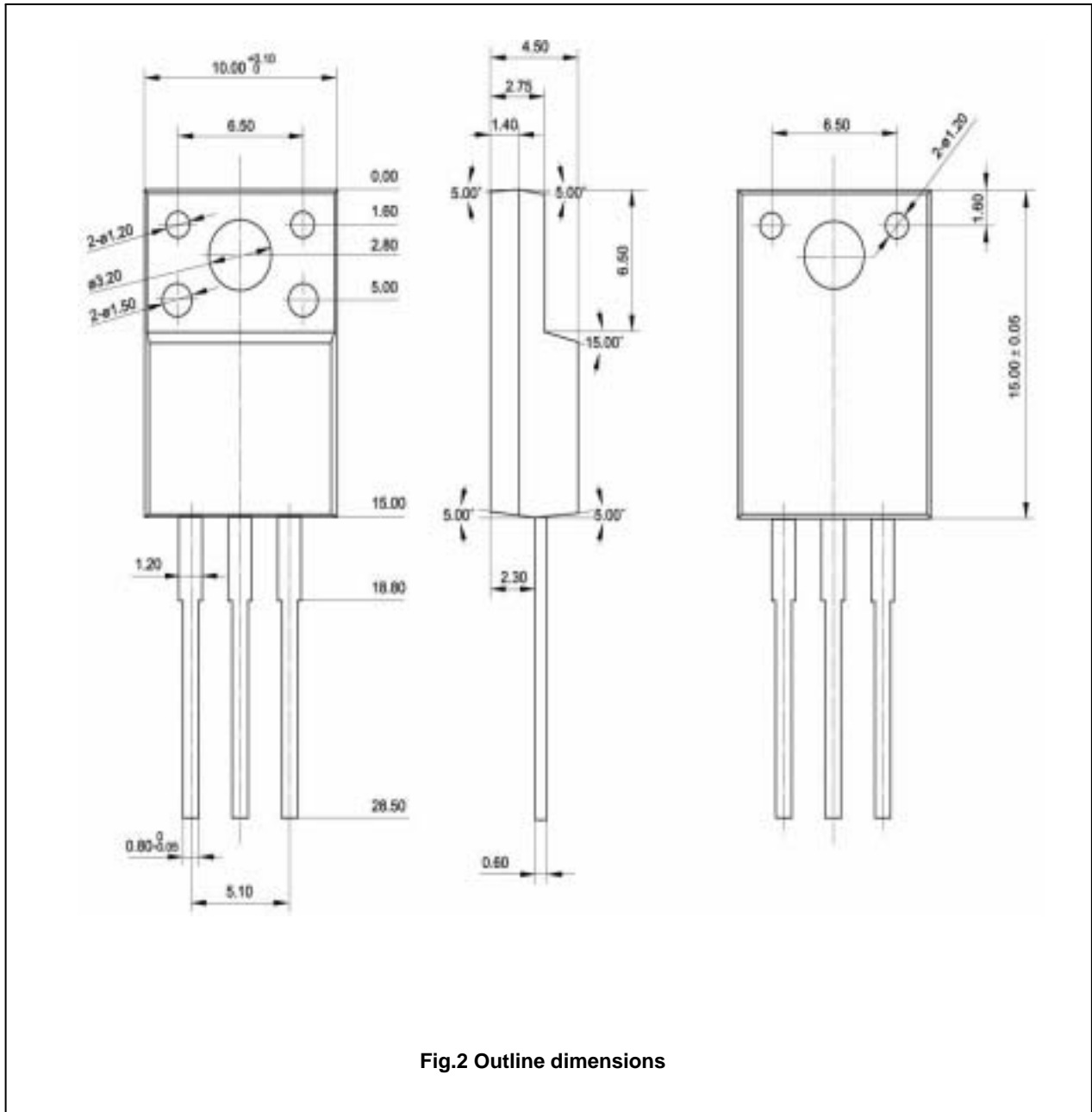


Fig.2 Outline dimensions

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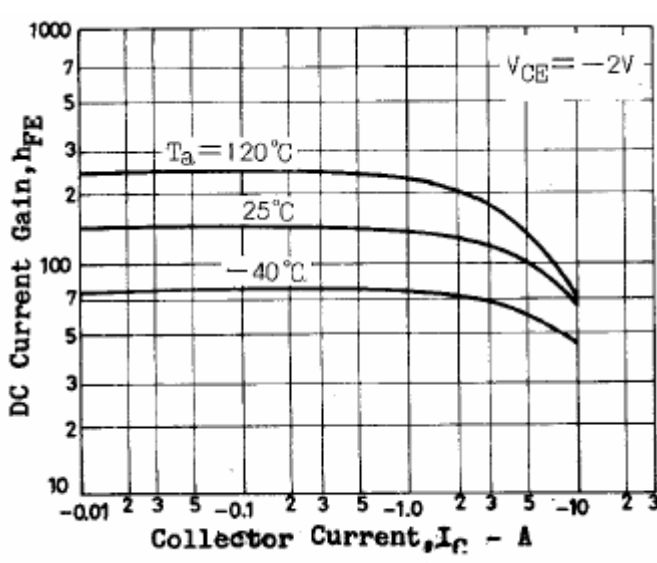


Fig.3 DC current Gain

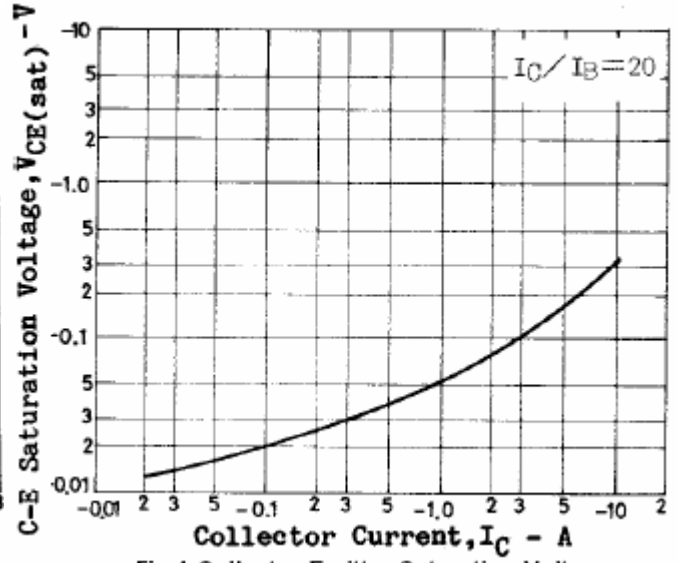


Fig.4 Collector-Emitter Saturation Voltage

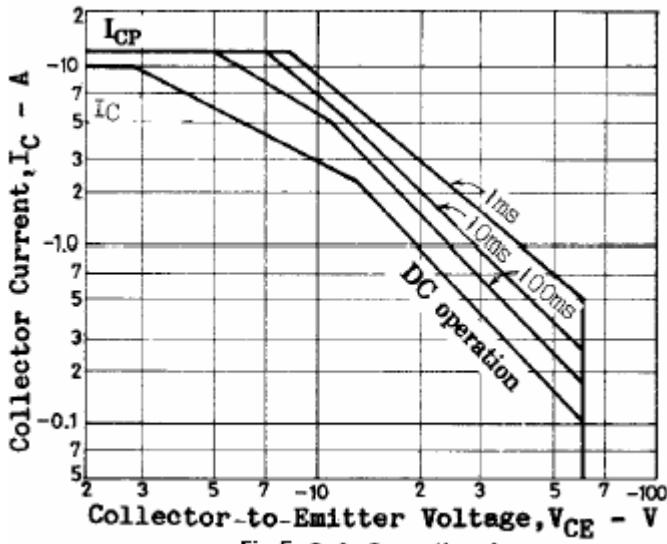


Fig.5 Safe Operating Area